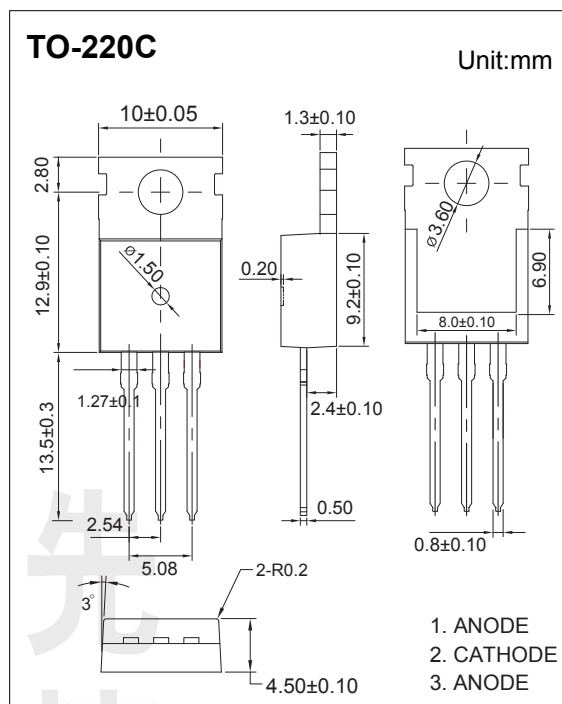


Schottky Barrier Rectifier MBR20200CT

■ Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V _{RRM}	200	V
Working peak reverse voltage	V _{RWM}		
DC blocking voltage	V _R		
RMS reverse voltage	V _{R(RMS)}	140	
Average rectified output current @T _C =125°C	I _O	20	A
Non-Repetitive peak forward surge current @ 8.3ms	I _{FSM}	150	
Power dissipation	P _D	2	W
Thermal resistance junction to ambient	R _{θJA}	50	°C/W
Junction temperature	T _J	125	°C
Storage temperature	T _{STG}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R =1mA	200			V
Reverse voltage leakage current	I _R	V _R =200V			100	μA
Forward voltage	V _F	I _F =10A			1	V
		I _F =20A			1.2	
Typical total capacitance	C _t	V _R =5V, f=1MHz		500		pF

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■ Typical Characteristics

